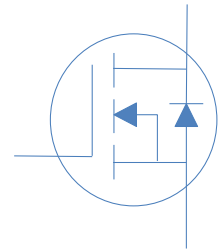


65V N-Ch Power MOSFET

V_{DS}	65	V
$R_{DS(on),typ}$	7.8	m
I_D (Silicon Limited)	57	A



Part Number	Package	Marking
HGD090NE6A	TO-252	GD090NE6A
HGI090NE6A	TO-251	GI090NE6A

Absolute Maximum Ratings at $T_J=25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^\circ\text{C}$	57	A
		$T_C=100^\circ\text{C}$	41	
Drain to Source Voltage	V_{DS}	-	65	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	270	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.4\text{mH}, T_C=25^\circ\text{C}$	45	mJ
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	63	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^\circ\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	R_{JA}	50	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-Case	R_{JC}	2.4	$^\circ\text{C}/\text{W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Static Characteristics

Parameter	Symbol		typ	Unit
		65		V
			4.0	
Zero Gate Voltage Drain Current		-	1	A
	$V_{GS}=0V, V_{DS}=60V, T_j=100^\circ\text{C}$	-	100	

Fig 1. Typical Output Characteristics

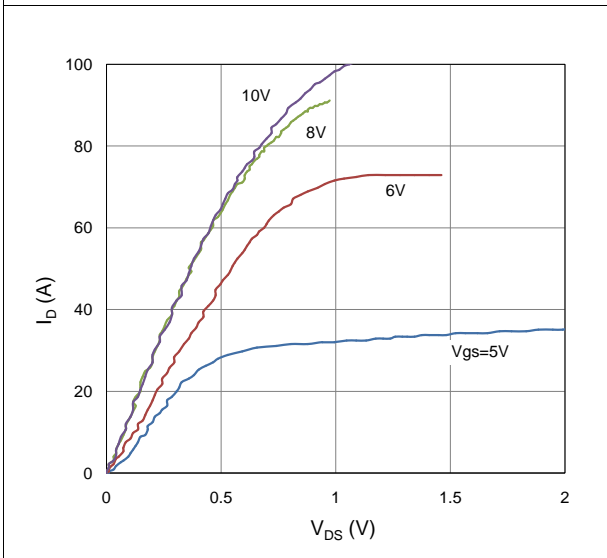


Figure 2. On-Resistance vs. Gate-Source Voltage

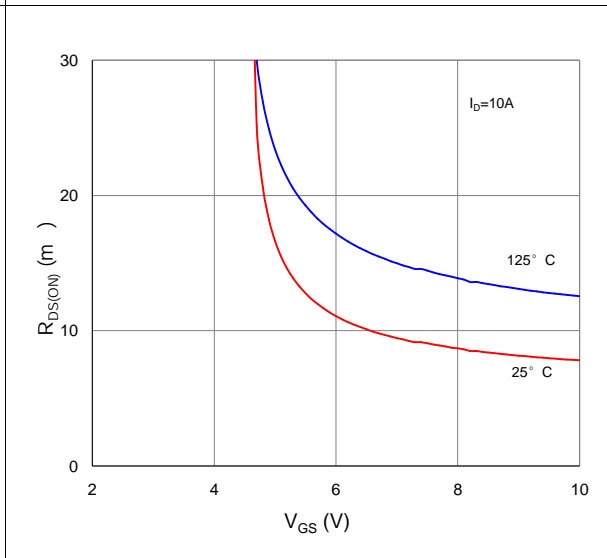


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

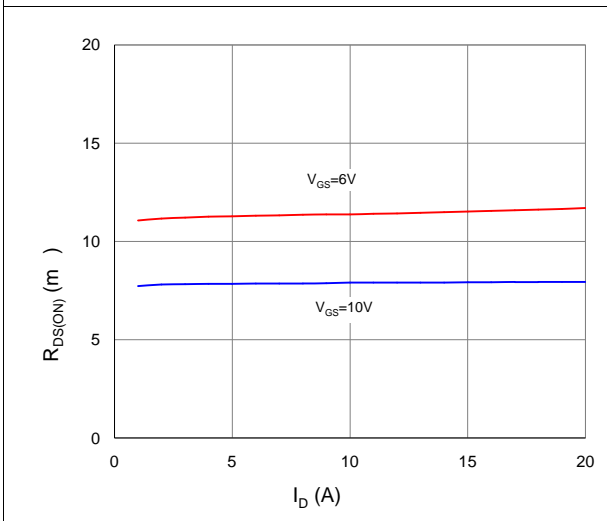


Figure 4. Normalized On-Resistance vs. Junction Temperature

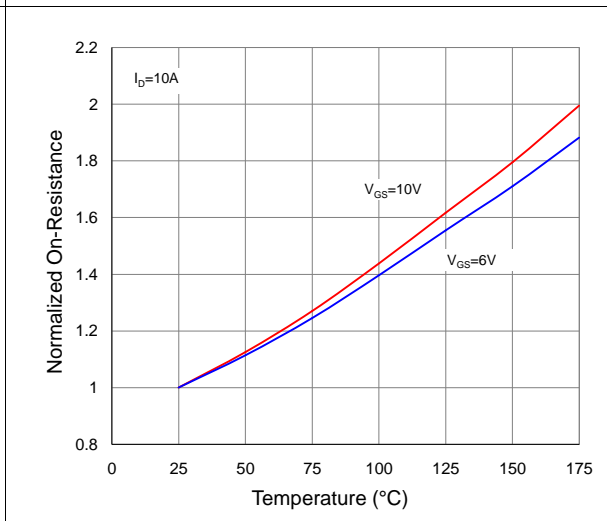


Figure 5. Typical Transfer Characteristics

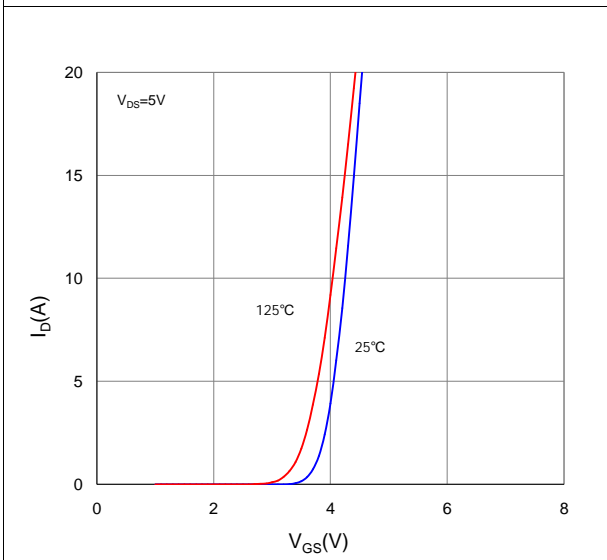


Figure 6. Typical Source-Drain Diode Forward Voltage

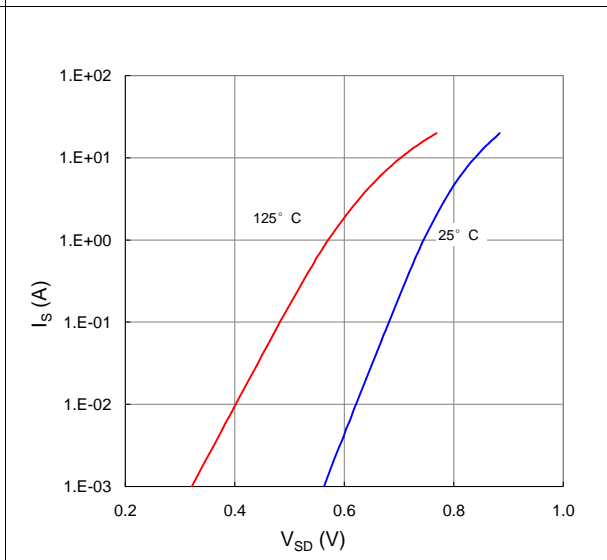


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

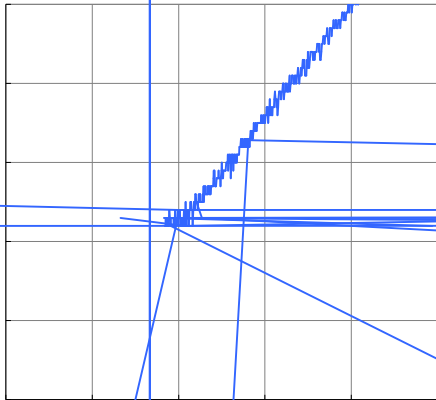


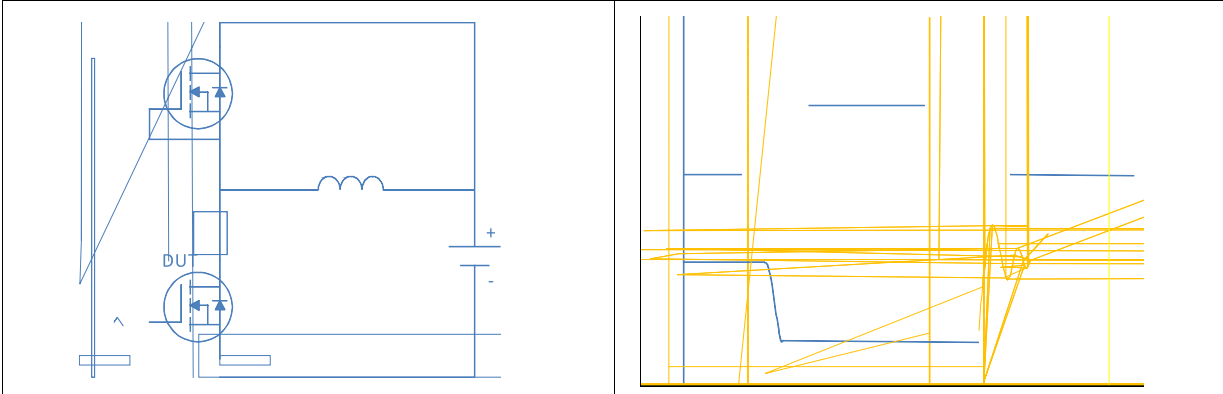
Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area

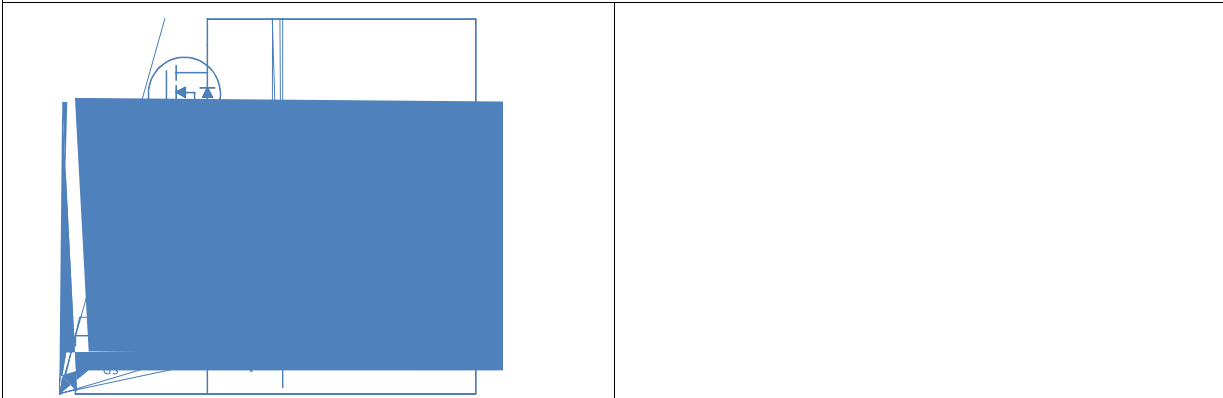
Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

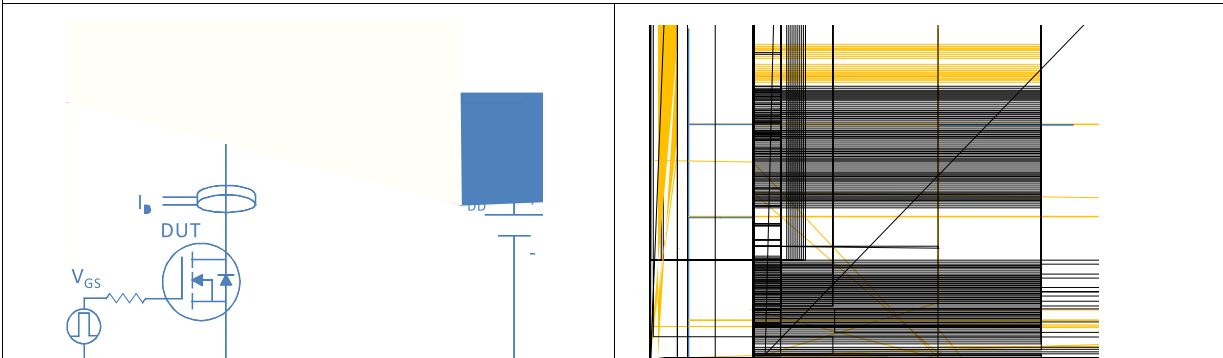
Inductive switching Test



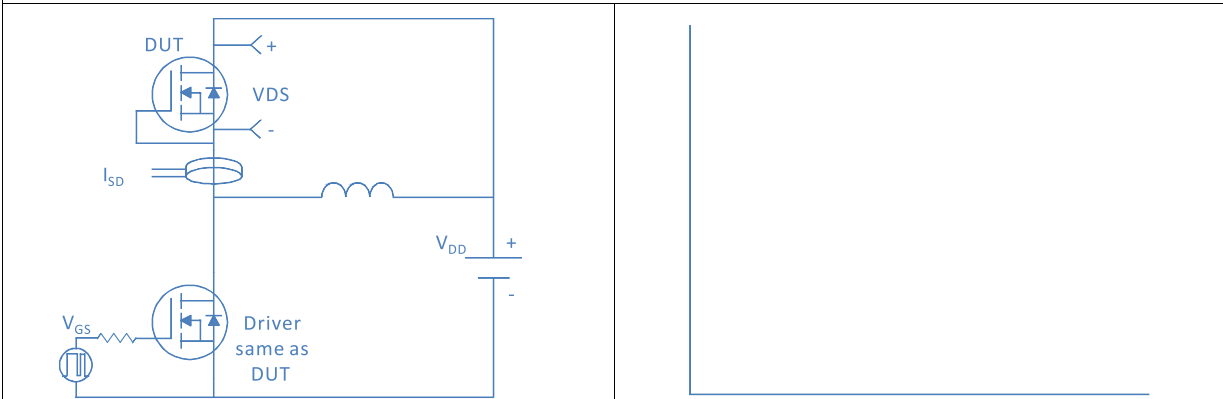
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

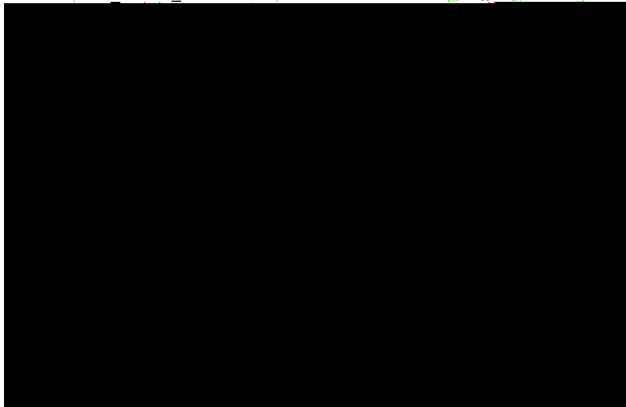


Diode Recovery Test

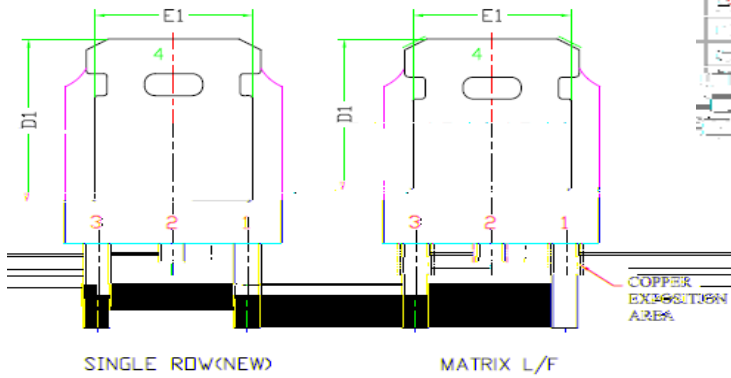


Package Outline

TO-252, 2 leads

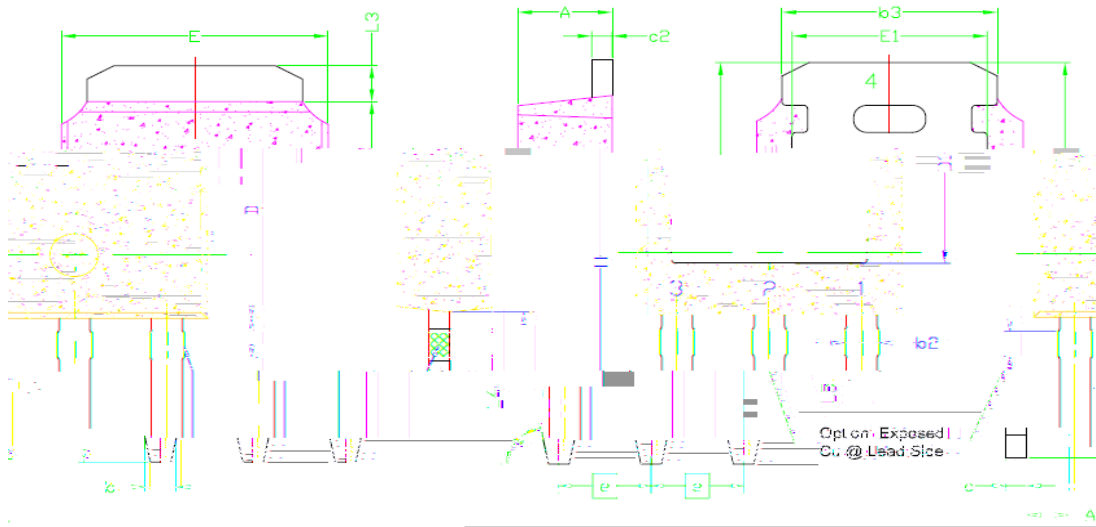


SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223



Package Outline

TO-251, 3leads



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	3.98	4.13	4.28
L3	0.89	--	1.27
L4	0.698 REF		
L5	0.972	1.099	1.226
D	6.00	6.10	6.223
H	11.05	11.25	11.45
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0.89	1.04	1.15
c	0.46	0.50	0.60
c2	0.46	0.50	0.60
D1	5.10	--	--
E1	4.40	--	--
a	79° REF		